

ABSTRACT

Memory device is made based upon a structure comprising a lamination of at least two thin pieces each having a periodically laminated configuration of conductive layers (preferably metals) each having a thickness in the range from 0.2 nm to 60 nm, and dielectric layers, each having a thickness larger than the thickness of each the conductive layer, such that the layers cross each other and edges of the conductive layers are opposed to each other. The thickness of said conductive layer is preferably in the range from 0.2 nm to 30 nm, and the thickness of said dielectric is typically in the range from 2 nm to 200 μ m. The recording medium is insulator layer or nano-bridge structure.



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